

Switching diode

1SS380

● Applications

Low leakage switching

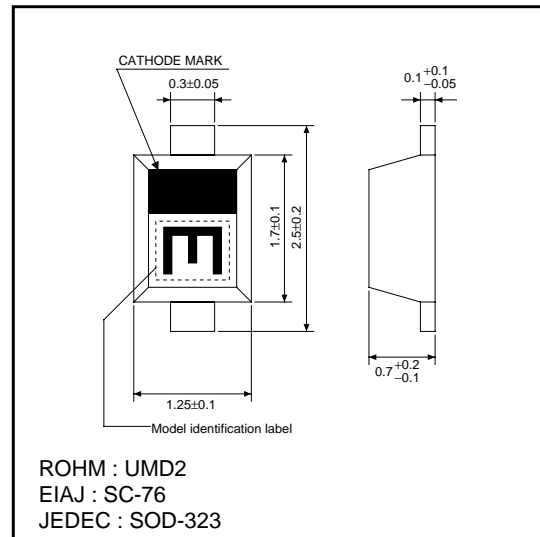
● Features

- 1) Small surface mounting type. (UMD2)
- 2) Ultra low I_R . ($I_R=40\text{pA Typ.}$)
- 3) High reliability.

● Construction

Silicon epitaxial planar

● External dimensions (Units : mm)



● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	35	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_o	100	mA
Surge current (1s)	I_{surge}	400	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+125	$^\circ\text{C}$

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	$I_F=100\text{mA}$
Reverse current	I_R	-	-	10	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T	-	-	5.0	pF	$V_R=0.5\text{V}$, $f=1\text{MHz}$

Diodes

●Electrical characteristic curves (Ta = 25°C)

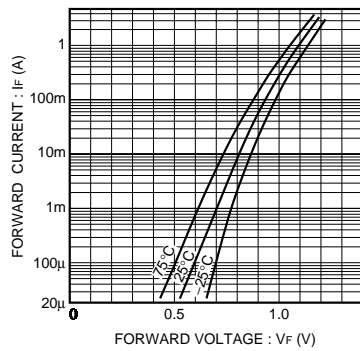


Fig. 1 Forward characteristics

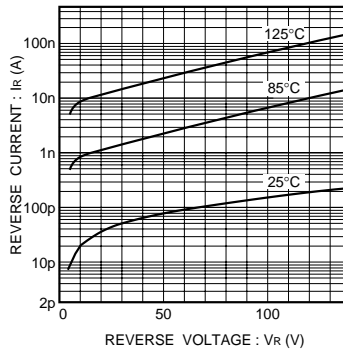


Fig. 2 Reverse characteristics

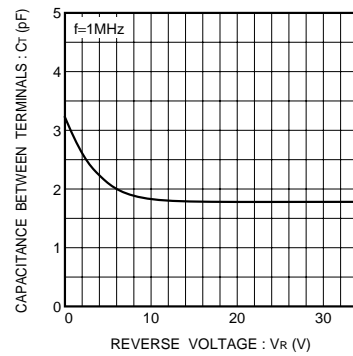


Fig. 3 Capacitance between terminals characteristics

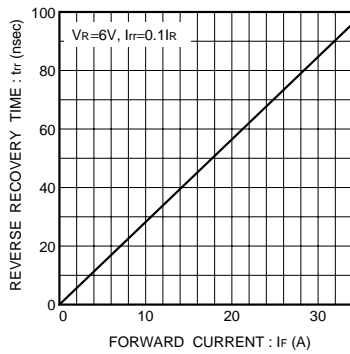


Fig. 4 Reverse recovery time characteristics

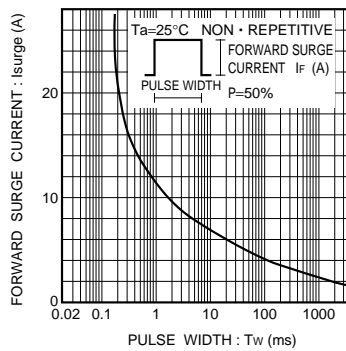


Fig. 5 Surge current characteristics

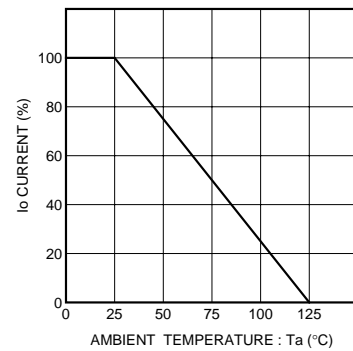


Fig. 6 Derating curve (mounting on glass epoxy PCBs)